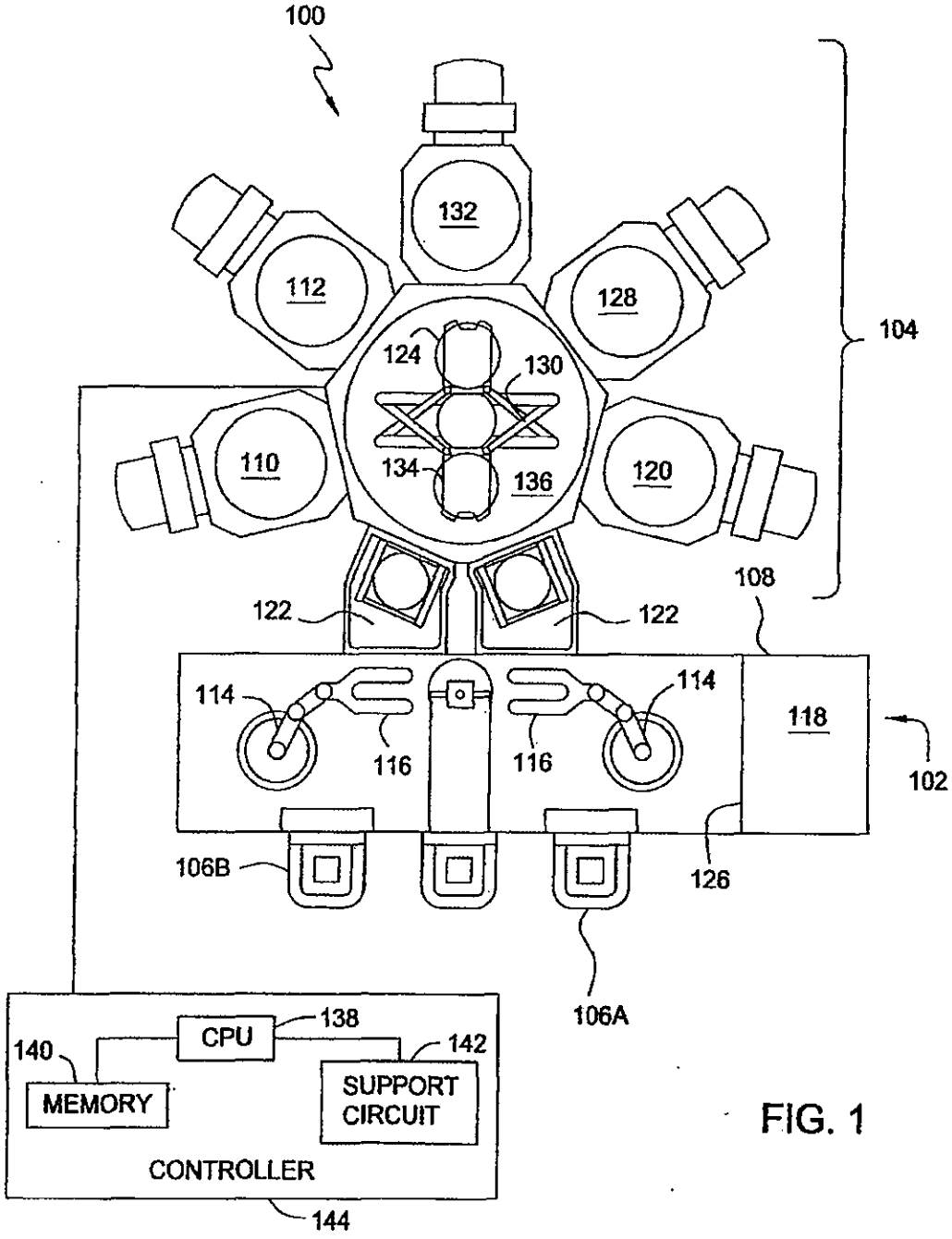

100
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112
128
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124
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136
120
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122
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114
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118
116
116
102
106B
126
106A
CPU
138
140
142
MEMORY
SUPPORT CIRCUIT
CONTROLLER
144

FIG. 1

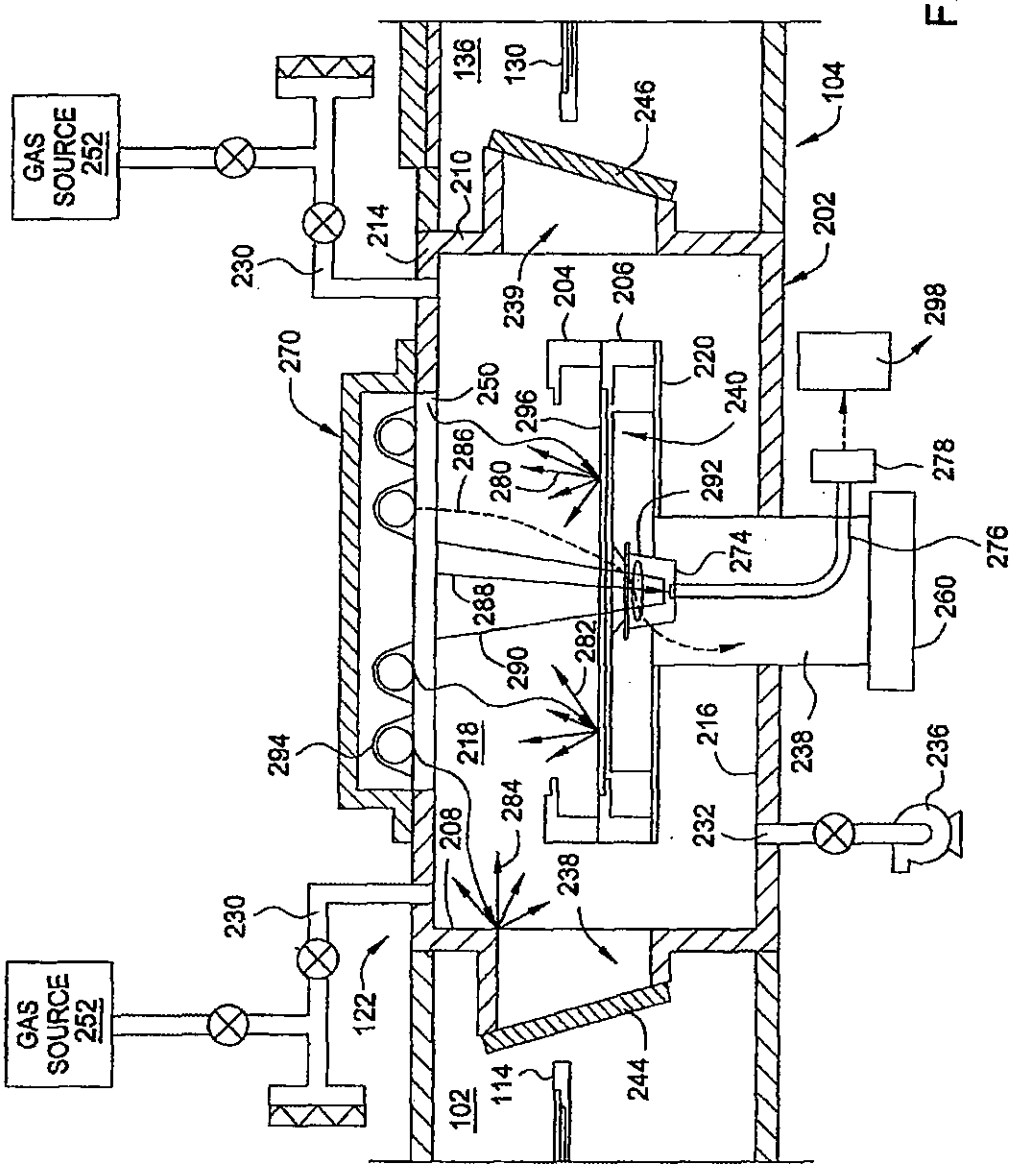
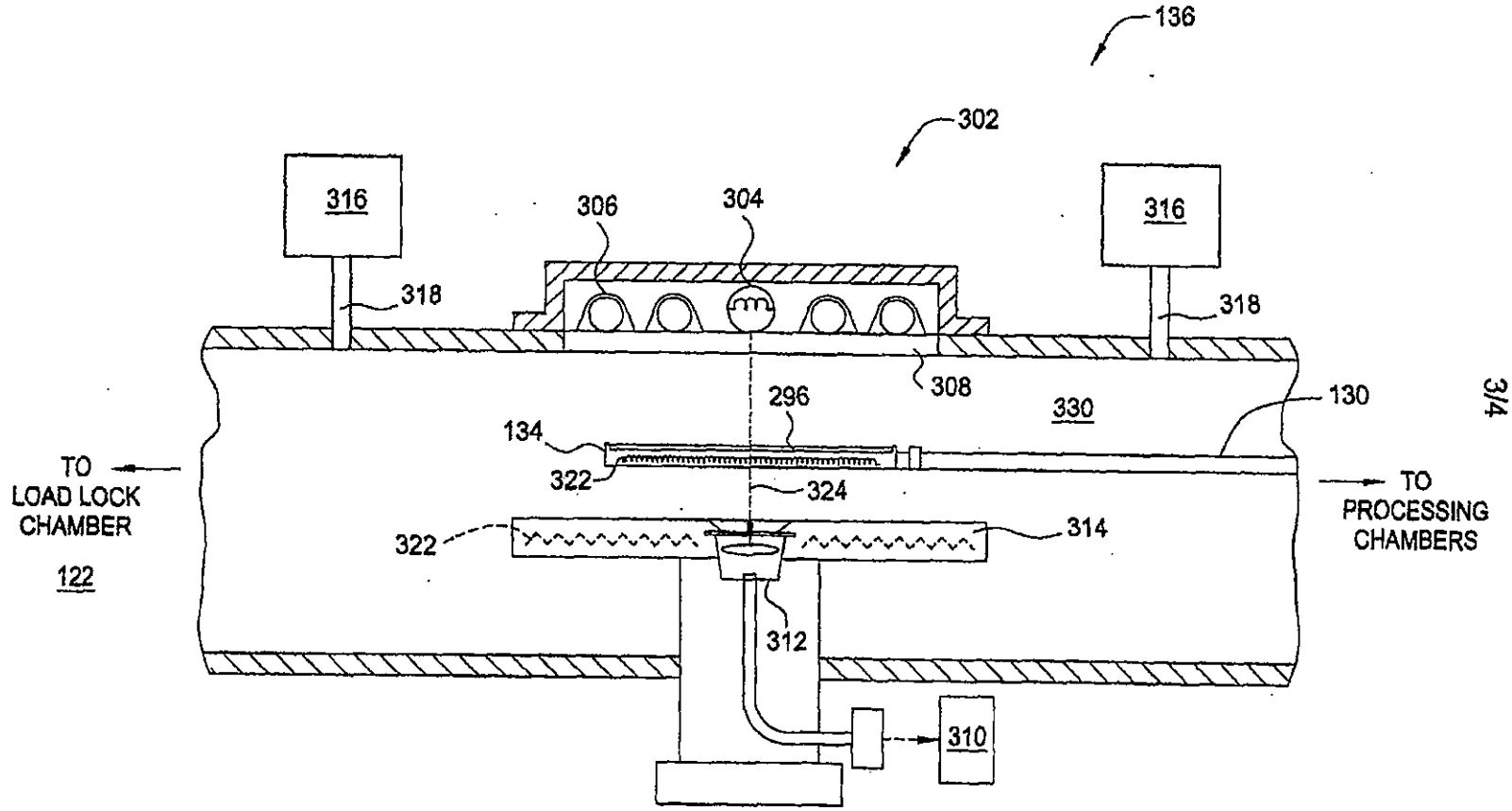

GAS SOURCE 252
GAS SOURCE 252
136
130
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210
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284
232
208
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230
122
244
102
114

FIG. 2

FIG. 3


136
302
316
306
304
316
318
318
308
296
330
130
134
322
324
TO
LOAD LOCK
CHAMBER
122
TO
PROCESSING
CHAMBERS
322
314
312
310

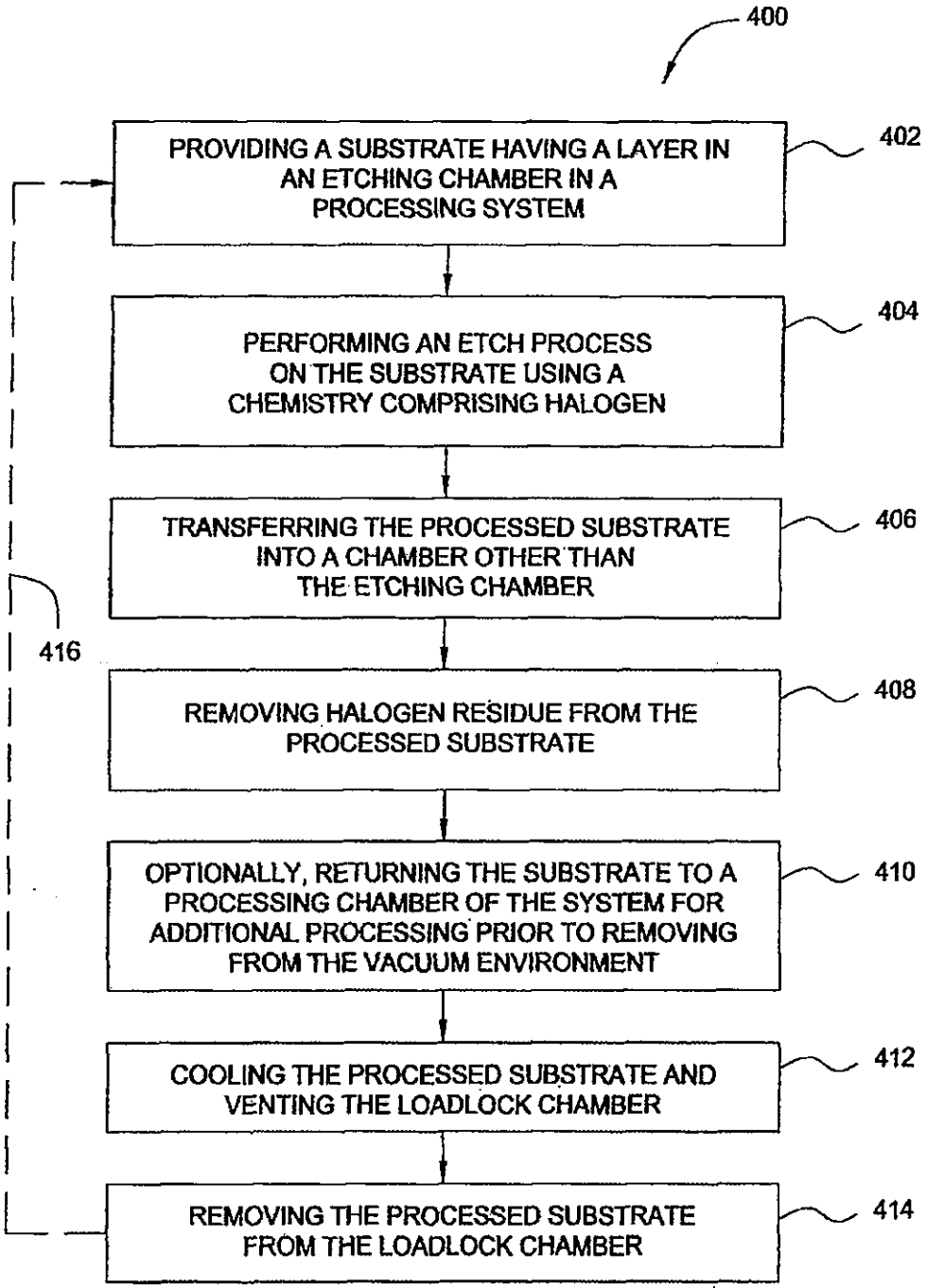

400
PROVIDING A SUBSTRATE HAVING A LAYER IN AN ETCHING CHAMBER IN A PROCESSING SYSTEM
402
PERFORMING AN ETCH PROCESS ON THE SUBSTRATE USING A CHEMISTRY COMPRISING HALOGEN
404
TRANSFERRING THE PROCESSED SUBSTRATE INTO A CHAMBER OTHER THAN THE ETCHING CHAMBER
406
416
REMOVING HALOGEN RESIDUE FROM THE PROCESSED SUBSTRATE
408
OPTIONALLY, RETURNING THE SUBSTRATE TO A PROCESSING CHAMBER OF THE SYSTEM FOR ADDITIONAL PROCESSING PRIOR TO REMOVING FROM THE VACUUM ENVIRONMENT
410
COOLING THE PROCESSED SUBSTRATE AND VENTING THE LOADLOCK CHAMBER
412
REMOVING THE PROCESSED SUBSTRATE FROM THE LOADLOCK CHAMBER
414

FIG. 4